

# HVR3509-H

PRV : 9000 Volts

Io : 350 mA

### FEATURES :

- \* Glass passivated junction chip
- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Pb / RoHS Free

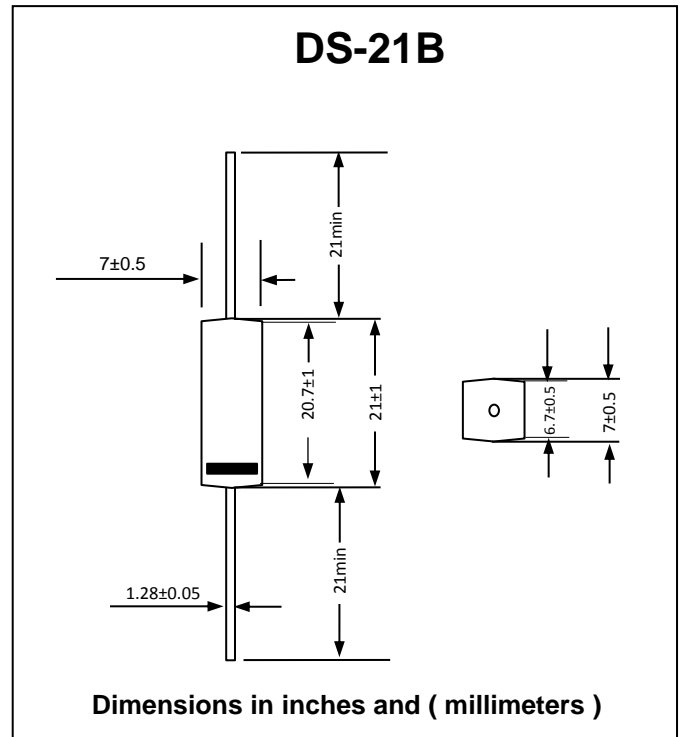
### APPLICATION :

- \* Micro-wave Oven

### MECHANICAL DATA :

- \* Case : DS-21B Molded plastic
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any

## HIGH VOLTAGE RECTIFIER DIODE



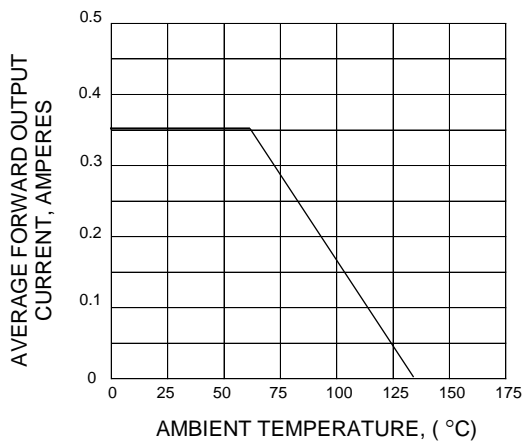
### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

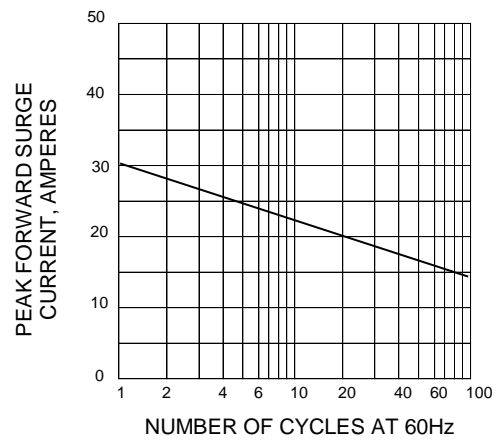
RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	9000	V
Maximum RMS Voltage	$V_{RMS}$	6300	V
Maximum DC Blocking Voltage	$V_{DC}$	9000	V
Maximum Average Forward Current	$I_{F(AV)}$	350	mA
Maximum Non-repetitive Peak Reverse Current	$I_{RSM}$	100	mA
Maximum Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on rated load	$I_{FSM}$	30	A
Maximum Peak Forward Voltage at $I_F = 350 \text{ mA}$	$V_F$	8.0	V
Avalanche Breakdown Voltage at $I_R = 100 \mu\text{A}$	$V_{(BR)}$	9.5	kV
Maximum DC Reverse Current at $V_{RM} = V_{RRM}$	$I_R$	5.0	$\mu\text{A}$
Junction Temperature Range	$T_J$	130	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-40 to +130	$^{\circ}\text{C}$

**RATING AND CHARACTERISTIC CURVES ( HVR3509-H )**

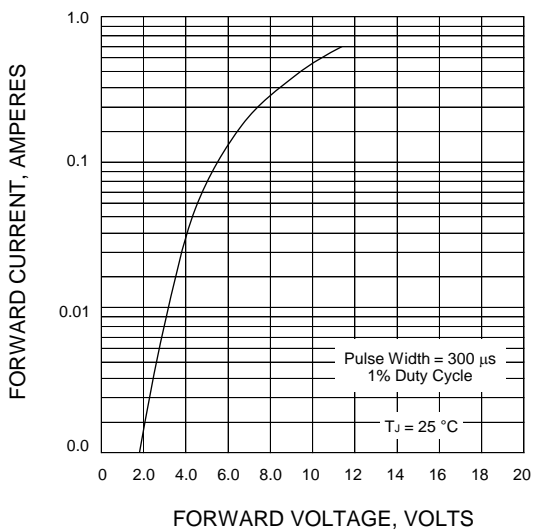
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

